



## *Future Normal in Semiconductor*

2025-02-13(목), 10:55-12:40

좌장: 추후업데이트 예정

### D. Thin Film Process Technology 분과

#### [TE2-D] Memory Capacitors

<p>TE2-D-1 10:55-11:10</p>	<p><b>Investigation of Atomic Layer Deposited SnO<sub>2</sub> Thin Films for Next-Generation DRAM Electrode Application</b> InHong Hwang<sup>1,2</sup> and In-Hwan Baek<sup>1,2</sup> 1Department of Chemistry and-Chemical Engineering, Inha University, <sup>2</sup>Program in Semiconductor Convergence, Inha University</p>
<p>TE2-D-2 11:10-11:25</p>	<p><b>Achieving Equivalent Oxide Thickness Scaling of ZrO<sub>2</sub> Dielectric Thin Film via Gd Doping without Sacrificing Tetragonal Crystallinity</b> Seungwoo Lee<sup>1,2</sup>, Jihun Nam<sup>1,2</sup>, Yoona Choi<sup>1,2</sup>, Jonghwan Jeong<sup>1,2</sup>, Min Kyeong Nam<sup>1,2</sup>, Hansol Oh<sup>3</sup>, Hanbyul Kim<sup>3</sup>, Yongjoo Park<sup>3</sup>, Youngjin Kim<sup>4</sup>, and Woojin jeon<sup>1,2</sup> <sup>1</sup>Department of Advanced Materials Engineering for Information and Electronics, Kyung Hee University, <sup>2</sup>Integrated Education Program for Frontier Science &amp; Technology, Kyung Hee University, <sup>3</sup>Advanced Research Development Team, SK Trichem Co., Ltd., <sup>4</sup>Department of Chemical Engineering, Kyonggi University</p>
<p>TE2-D-3 11:25-11:40</p>	<p><b>Influence of Zr-Precursor Ligands on the Growth and Capacitor Properties of ZrO<sub>2</sub> Thin Films Grown by ALD</b> Hyeongjun Kim<sup>1</sup>, Haram Yang<sup>2</sup>, and Woongkyu Lee<sup>1,2</sup> <sup>1</sup>Department of Green Chemistry and Materials Engineering, Soongsil University, <sup>2</sup>Department of Materials Science and Engineering, Soongsil University</p>
<p>TE2-D-4 11:40-11:55</p>	<p><b>Strategy for Stabilizing Metastable Rutile-Structured TiO<sub>2</sub> without Substrate Crystallographic Limitations</b> Jihoon Jeon<sup>1,2</sup> and Seong Keun Kim<sup>1,2</sup> <sup>1</sup>Electronic Materials Research Center, KIST, <sup>2</sup>KU-KIST Graduate School of Converging Science and Technology, Korea University</p>
<p>TE2-D-5 11:55-12:10</p>	<p><b>High Performance TiO<sub>2</sub>-based DRAM Capacitors with Ultrathin ALD Sn-Doped MoO<sub>2</sub>Buffer Layer</b> Jae Hyeon Lee and Jeong Hwan Han Department of Materials Science and Engineering, Seoul National University of Science and Technology</p>



## *Future Normal in Semiconductor*

<p>TE2-D-6 12:10-12:25</p>	<p><b>Dielectrics with Sub-surface Dopant Implantation-Mediated Lattice Relaxation and <math>V_0</math> Annihilation via Chemo-physical Plasma Annealing</b> Gyuha Lee<sup>1</sup>, Hyongjune Kim<sup>1</sup>, Geongu Han<sup>2</sup>, Sangwon Lee<sup>3</sup>, Jeongmin Oh<sup>3</sup>, and Jihwan An<sup>1,3</sup> <sup>1</sup>Department of Mechanical Engineering, POSTECH, <sup>2</sup>Department of Manufacturing Systems and Design Engineering, Seoul National University of Science and Technology, <sup>3</sup>Graduate School of Semiconductor Technology, POSTECH</p>
<p>TE2-D-7 12:25-12:40</p>	<p><b>Synthesis of Perovskite <math>SrTiO_3</math> Thin Films by Atomic Layer Deposition of <math>SrF_2</math> and <math>TiO_2</math></b> Jaejun Lee, Sangyeon Jeong, and Woongkyu Lee Department of Materials Science and Engineering, Soongsil University</p>